

SANGDEST MICROELECTRONICS

SDURF1040CT(CTR)

Technical Data Data Sheet N0175, Rev. A

Green Products

SDURF1040CT(CTR) ULTRAFAST PLASTIC RECTIFIER

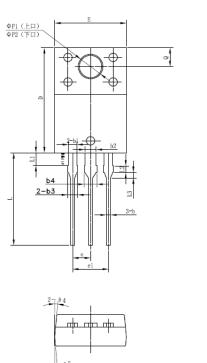
Applications:

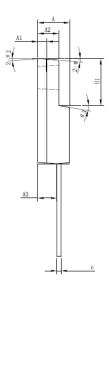
- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Features:

- Fully Molded Isolation
- Dual Diodes-Anode Common
- Ultra-Fast Recovery
- Low Forward Voltage Drop
- High Surge Capability
- 200 Volts thru 600 Volts Types Available
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm

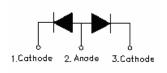




SYMBOL	MIN.	TYP.	MAX.
Α	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00 2.70	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85
С	0.55	0.60	0.75
D E	14.80	15.00	15.20
E	9.96	10.16	10.36
е		2.55	
e1		5.10	
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L1 L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦΡ1(上口)	3.30 2.99	3.50	3.70
ΦΡ2 (下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

ITO-220AB





SDURF1040CT

SDURF1040CTR



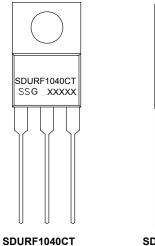
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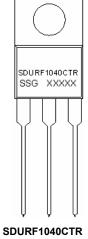
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Marking Diagram:





Where XXXXX is YYWWL

SDUR	= Device Type
F	= Package Type
10	= Forward Current (10A)
40	= Reverse Voltage (400V)
CT/CTR	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
SDURF1040CT/CTR	ITO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	400	V
Max. Average Forward	lo _(AV)	50Hz, Sine wave, T _C =112 $^{\circ}$ C	10	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	50Hz, Half Sine wave	80	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop(per leg)	V_{F}	@ I _F = 5A, Pulse, T _J = 25℃	1.3	V
Max. Reverse Current	I _R	@V _R = rated V _R T _J = 25℃	30	μA
Max. Reverse Recovery Time	t _{rr}	I_F =500mA, I_R =1A,and I_{rm} =250mA	45	ns

* Pulse width < 300 μ s, duty cycle < 2%

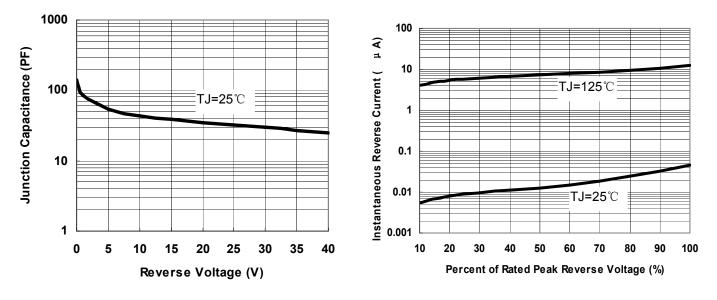
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	TJ	-	-55 to +150	°C
Max. Storage Temperature	T _{stg}	-	-55 to +150	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	3.5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			



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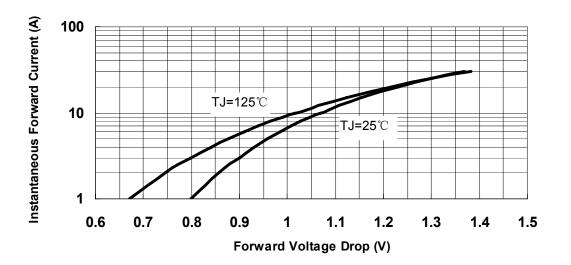


Fig.3-Typical Instantaneous Forward Voltage Characteristics



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2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

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